MOSFET - SiC Power, Single N-Channel

1200 V, 80 mΩ, 31 A

NVHL080N120SC1A

Features

- Typ. $R_{DS(on)}$ = 80 mΩ
- Ultra Low Gate Charge (typ. $Q_{G(tot)}$ = 56 nC)
- Low Effective Output Capacitance (typ. C_{oss} = 80 pF)
- 100% UIL Tested
- Qualified According to AEC−Q101
- These Devices are RoHS Compliant

Typical Applications

- Automotive On Board Charger
- Automotive DC/DC converter for EV/HEV

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	1200	V
Gate−to−Source Voltage			V_{GS}	−15/+25	V
Recommended Operation Values of Gate−to−Source Voltage	T_C < 175°C		V_{GSop}	−5/+20	V
Continuous Drain Current $R_{\theta JC}$	Steady State	T_C = 25°C	I_D	31	A
Power Dissipation $R_{\theta JC}$			P_D	178	W
Continuous Drain Current $R_{\theta JC}$	Steady State	T_C = 100°C	I_D	22	A
Power Dissipation $R_{\theta JC}$			P_D	89	W
Pulsed Drain Current (Note 2)	T_A = 25°C		I_{DM}	132	A
Single Pulse Surge Drain Current Capability	T_A = 25°C, t_p = 10 μs, R_G = 4.7 Ω		I_{DSC}	132	A
Operating Junction and Storage Temperature Range			T_J, T_{stg}	−55 to +175	°C
Source Current (Body Diode)			I_S	18	A
Single Pulse Drain−to−Source Avalanche Energy ($I_{L(pk)}$ = 18.5 A, L = 1 mH) (Note 3)			E_{AS}	171	mJ

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction−to−Case (Note 1)	$R_{\theta JC}$	0.84	°C/W
Junction−to−Ambient (Note 1)	$R_{\theta JA}$	40	°C/W

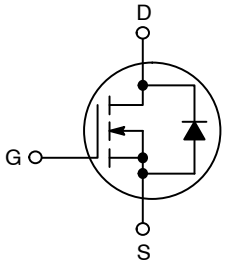
1. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.
2. Repetitive rating, limited by max junction temperature.
3. E_{AS} of 171 mJ is based on starting T_J = 25°C; L = 1 mH, I_{AS} = 18.5 A, V_{DD} = 120 V, V_{GS} = 18 V.

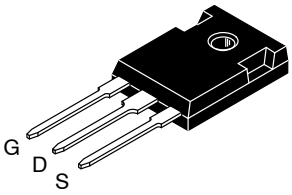
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$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
1200 V	110 mΩ @ 20 V	31 A

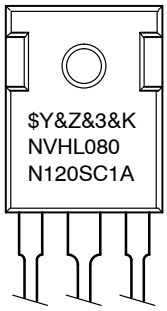
N−CHANNEL MOSFET





TO−247−3LD
CASE 340CX

MARKING DIAGRAM



$Y = ON Semiconductor Logo
&Z = Assembly Plant Code
&3 = Data Code (Year & Week)
&K = Lot
NVHL080N120SC1A = Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

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ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1 mA	1200	–	–	V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	I_D = 1 mA, referenced to 25°C	–	700	–	mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = 1200 V, T_J = 25°C	–	–	100	μA
		V_{GS} = 0 V, V_{DS} = 1200 V, T_J = 175°C	–	–	1	mA
Gate−to−Source Leakage Current	I_{GSS}	V_{GS} = +25/−15 V, V_{DS} = 0 V	–	–	±1	μA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(th)}$	V_{GS} = V_{DS}, I_D = 5 mA	1.8	2.7	4.3	V
Recommended Gate Voltage	V_{GOP}		−5	–	+20	V
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 20 V, I_D = 20 A, T_J = 25°C	–	80	110	mΩ
		V_{GS} = 20 V, I_D = 20 A, T_J = 150°C	–	114	–	
Forward Transconductance	g_{FS}	V_{DS} = 20 V, I_D = 20 A	–	13	–	S
CHARGES, CAPACITANCES & GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 800 V	–	1112	–	pF
Output Capacitance	C_{OSS}		–	80	–	
Reverse Transfer Capacitance	C_{RSS}		–	6.5	–	
Total Gate Charge	$Q_{G(tot)}$	V_{GS} = −5/20 V, V_{DS} = 600 V, I_D = 20 A	–	56	–	nC
Gate−to−Source Charge	Q_{GS}		–	11	–	
Gate−to−Drain Charge	Q_{GD}		–	12	–	
Gate Resistance	R_G	f = 1 MHz	–	1.7	–	Ω
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	$t_{d(on)}$	V_{GS} = −5/20 V, V_{DS} = 800 V, I_D = 20 A, R_G = 4.7 Ω, Inductive Load	–	13	–	ns
Rise Time	t_r		–	20	–	
Turn−Off Delay Time	$t_{d(off)}$		–	22	–	
Fall Time	t_f		–	10	–	
Turn-On Switching Loss	E_{ON}		–	258	–	μJ
Turn-Off Switching Loss	E_{OFF}		–	52	–	
Total Switching Loss	E_{TOT}		–	311	–	
DRAIN−SOURCE DIODE CHARACTERISTICS						
Continuous Drain−to−Source Diode Forward Current	I_{SD}	V_{GS} = −5 V, T_J = 25°C	–	–	18	A
Pulsed Drain−to−Source Diode Forward Current (Note 2)	I_{SDM}	V_{GS} = −5 V, T_J = 25°C	–	–	132	A
Forward Diode Voltage	V_{SD}	V_{GS} = −5 V, I_{SD} = 10 A, T_J = 25°C	–	4	–	V
Reverse Recovery Time	t_{RR}	V_{GS} = −5/20 V, I_{SD} = 20 A, dI_S/dt = 1000 A/μs	–	16	–	ns
Reverse Recovery Charge	Q_{RR}		–	62	–	nC
Reverse Recovery Energy	E_{REC}		–	5	–	μJ
Peak Reverse Recovery Current	I_{RRM}		–	8	–	A

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS T_J = 25°C unless otherwise noted

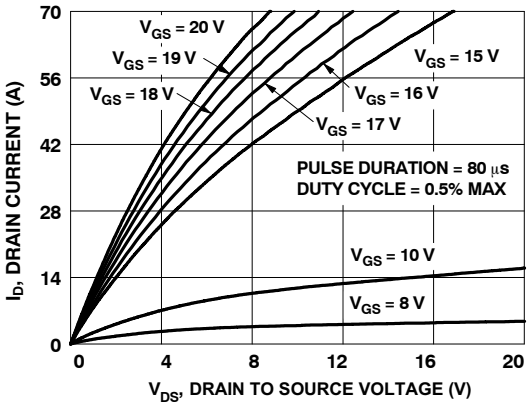


Figure 1. On Region Characteristics

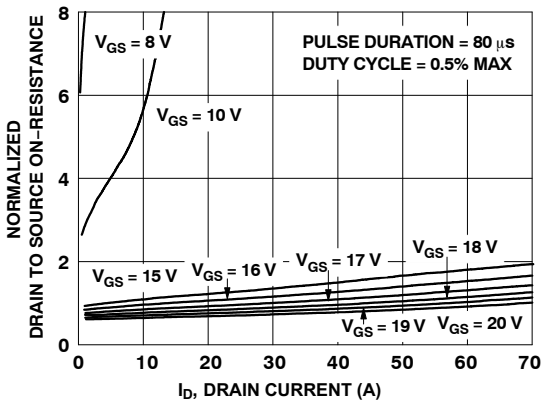


Figure 2. Normalized On−Resistance vs. Drain Current and Gate Voltage

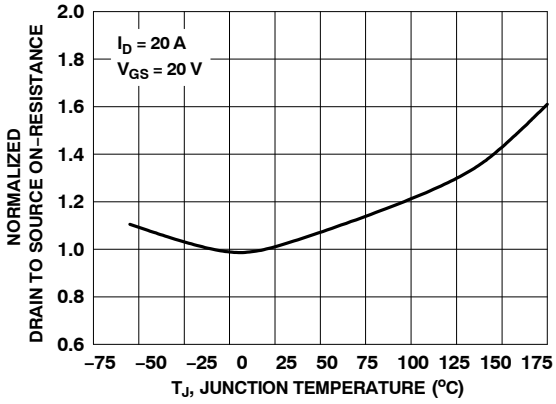


Figure 3. Normalized On Resistance vs. Junction Temperature

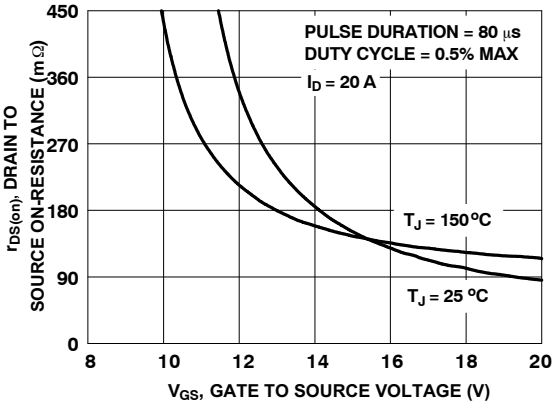


Figure 4. On−Resistance vs. Gate−to−Source Voltage

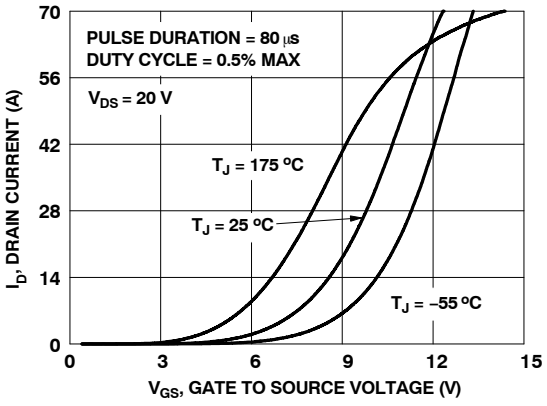


Figure 5. Transfer Characteristics

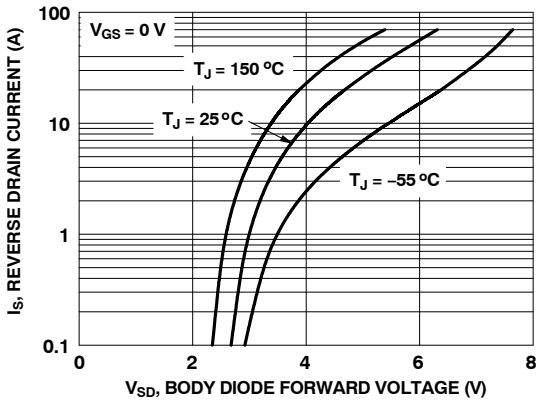


Figure 6. Source−to−Drain Diode Forward Voltage vs. Source Current

TYPICAL CHARACTERISTICS T_J = 25°C unless otherwise noted

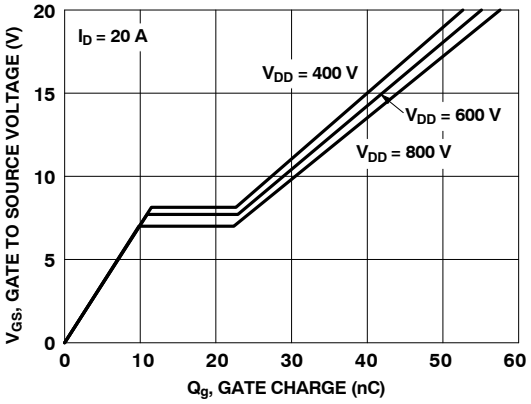


Figure 7. Gate Charge Characteristics

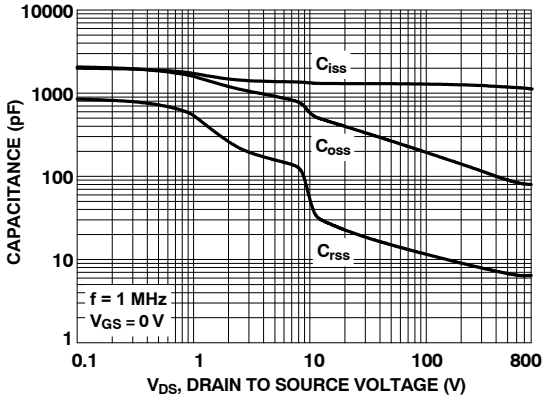


Figure 8. Capacitance vs. Drain−to−Source Voltage

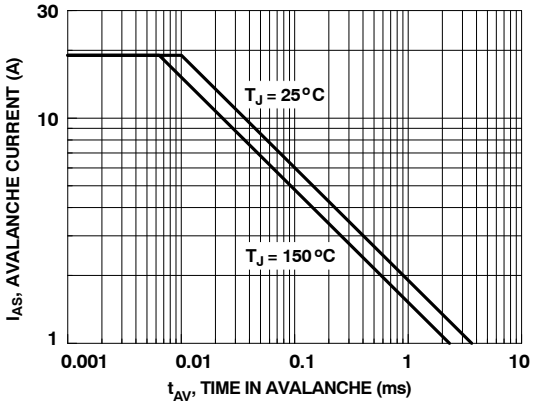


Figure 9. Unclamped Inductive Switching Capability

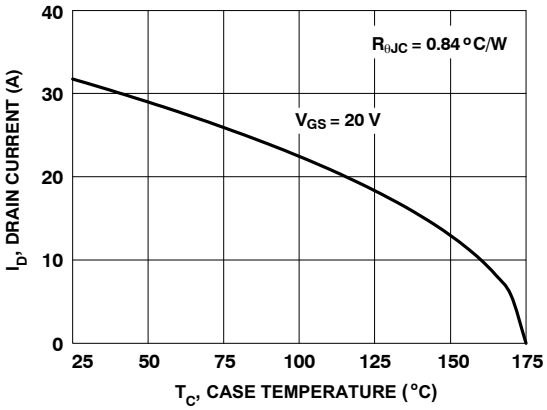


Figure 10. Maximum Continuous Drain Current vs. Case Temperature

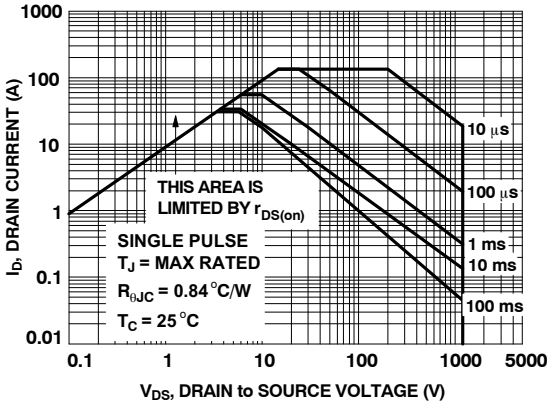


Figure 11. Forward Bias Safe Operating Area

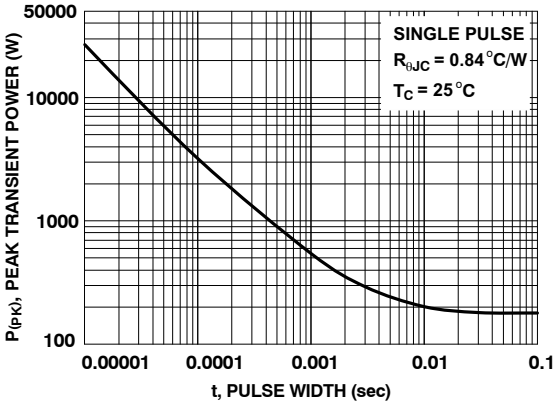


Figure 12. Single Pulse Maximum Power Dissipation

TYPICAL CHARACTERISTICS T_J = 25°C unless otherwise noted

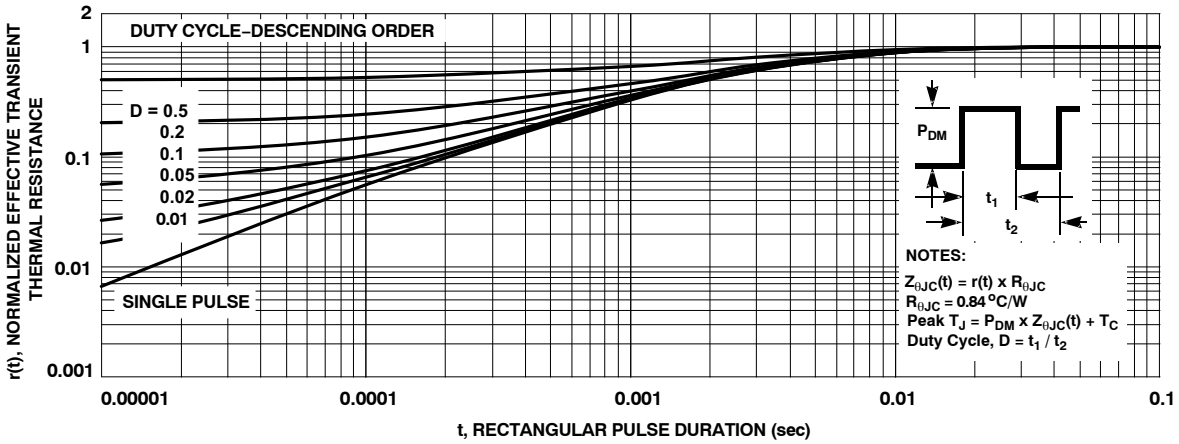


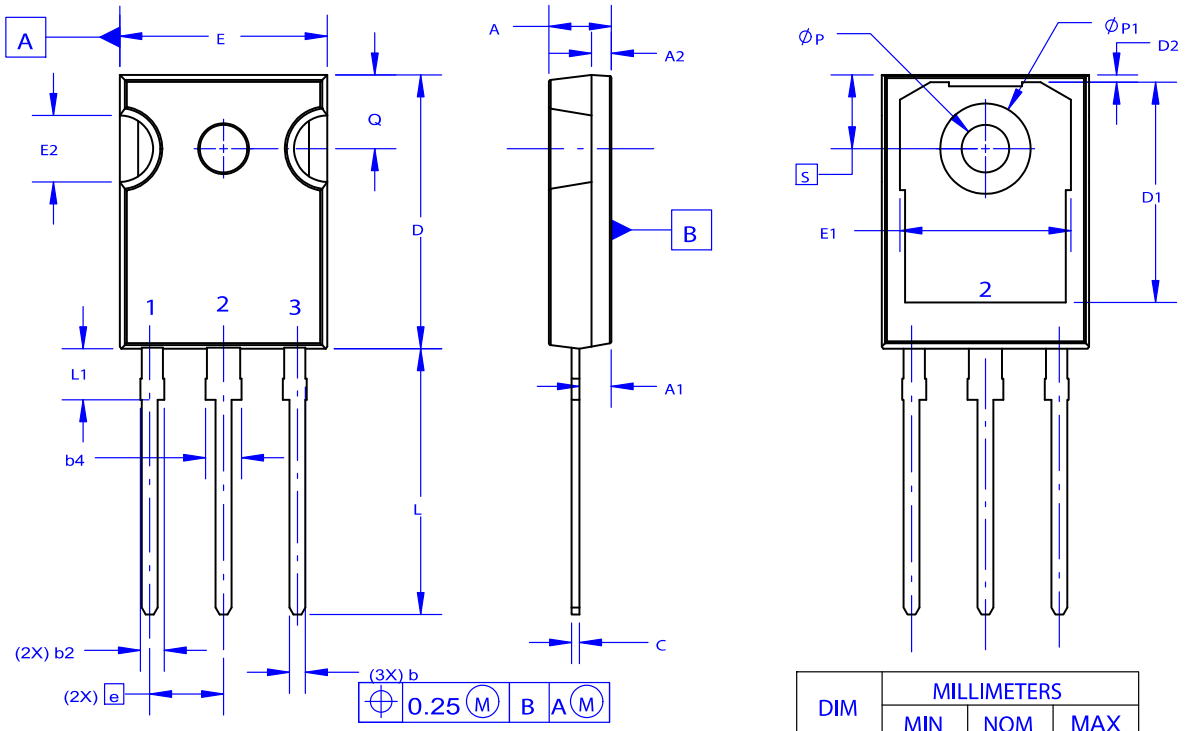
Figure 13. Junction−to−Case Transient Thermal Response Curve

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
NVHL080N120SC1A	NVHL080N120SC1A	TO−247 Long Lead	Tube	N/A	N/A	30 Units

PACKAGE DIMENSIONS

TO−247−3LD
CASE 340CX
ISSUE O



NOTES: UNLESS OTHERWISE SPECIFIED.

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ØP1	6.60	6.80	7.00

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